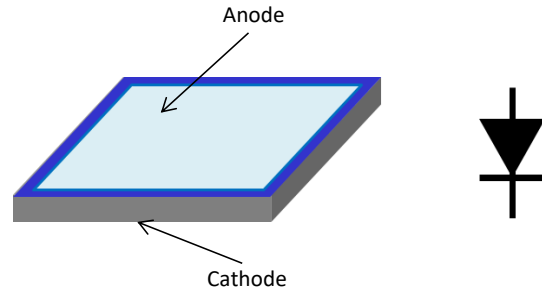


YJ Planar Schottky Barrier Diode Die Specification

40V 0.1A, 11mil, Schottky barrier diode die based on silicon planar process
 Part No.: PSB011L040AG-155A

Main Products Characteristics

- Average forward current: $I_{F(AV)} = 0.1A$
- Maximum operating junction temperature: $T_j = 125\text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um



Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	40 V
Average forward current	$I_{F(AV)}$	0.1A
Non-repetitive peak surge current ($t_p = 8.3\text{ ms}$, halfwave, 1 cycle)	I_{FSM}	1 A
Storage temperature range	T_{stg}	-50 to +125 $^\circ\text{C}$
Maximum operating junction temperature	T_j	125 $^\circ\text{C}$

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 100\mu\text{A}$	V_{BR}	46 V	54V
Maximum forward voltage drop $I_F = 10\text{mA}$ Pulse Test: $t_p = 800\ \mu\text{s}$, $\delta \leq 2\%$	V_F	0.43V	0.38V
Maximum reverse current $V_R = 10\text{V}$ Pulse Test: $t_p = 200\ \mu\text{s}$, $\delta \leq 2\%$	I_R	400nA	35nA

Device Schematics and Outline Drawing

Die Thickness *	155um
Die Size **	280um
Top Metal Pad	210um
Active Area	120um
Top Metal	AL/3.915um
Back Metal	Au/1.2um
Steet width	70um

Important Notice

<p>Specification apply to die only. Actual performance may degrade when assembled.</p> <p>Yangjie Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.</p> <p>Data sheet information is subjected to change without notice.</p>	<p>Recommended Storage Environment:</p> <p>Store in original container, in dessicated nitrogen, with no contamination.</p> <p>Shelf life for parts stored in above condition is 2 years.</p> <p>If the storage is done in normal atmosphere shelf life is reduced to 6 months.</p>
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